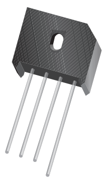
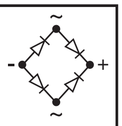
CBR4M-L010 SERIES

SILICON BRIDGE RECTIFIER
4 AMP, 100 THRU 1000 VOLTS





CASE DM

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CBR4M-L010 series types are single phase, full wave silicon bridge rectifiers designed for general purpose, high current applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

		CBR4M						
	SYMBOL	**-L010**	**-L020**	**-L040**	**-L060**	**-L080**	**-L100**	**UNITS**
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current	I_O	4.0						A
Average Forward Current (T_C=100°C)	I_O	8.0						A
Peak Forward Surge Current	I_{FSM}	300						A
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150						°C
Thermal Resistance	Θ_{JC}	3.5						°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_R	V_R=Rated V_{RRM}		10	μA
V_F	I_F=6.28A		1.1	V

R3 (26-June 2012)

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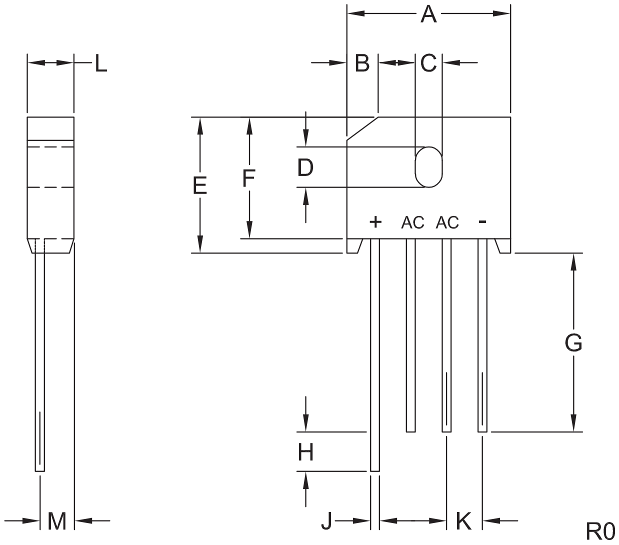
CASE DM - MECHANICAL OUTLINE



MARKING:
FULL PART NUMBER

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.895	0.935	22.73	23.75
B	0.165	0.185	4.19	4.70
C	0.140	0.160	3.56	4.06
D	0.215	0.235	5.46	5.97
E	-	0.760	-	19.30
F	0.660	0.700	16.76	17.78
G	1.000	-	25.40	-
H	0.180	0.260	4.57	6.60
J (DIA)	0.048	0.052	1.22	1.32
K	0.180	0.220	4.57	5.59
L	0.165	0.280	4.19	7.11
M	0.180	0.205	4.57	5.21

CASE DM (REV: R0)